

# PSMN6R0-30YL

## N-channel TrenchMOS logic level FET

Rev. 03 — 4 Januari 2010

Product data sheet

## 1. Product profile

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in industrial and communications applications.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

### 1.3 Applications

- Class-D amplifiers
- Motor control
- DC-to-DC converters
- Server power supplies

### 1.4 Quick reference data

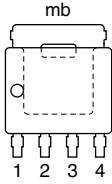
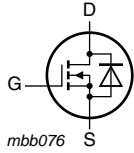
Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ }^{\circ}\text{C}$ ; $T_j \leq 175\text{ }^{\circ}\text{C}$	-	-	30	V
$I_D$	drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a>	-	-	79	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 2</a>	-	-	55	W
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5\text{ V}$ ; $I_D = 10\text{ A}$ ; $V_{DS} = 12\text{ V}$ ; see <a href="#">Figure 14</a> and <a href="#">15</a>	-	3.08	-	nC
$Q_{G(tot)}$	total gate charge		-	11	-	nC
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_j = 25\text{ }^{\circ}\text{C}$	-	4.26	6	m $\Omega$



## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

**SOT669 (LPAK)**

## 3. Ordering information

**Table 3. Ordering information**

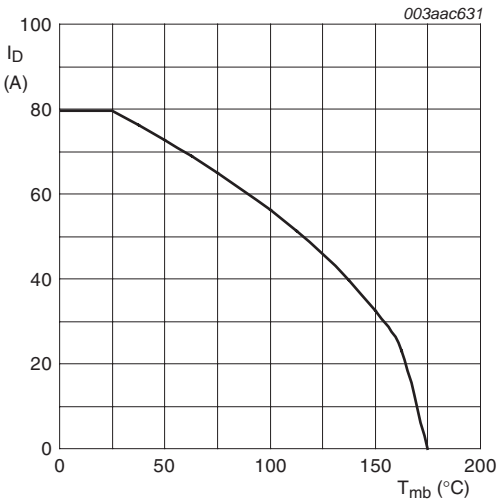
Type number	Package		Version
	Name	Description	
PSMN6R0-30YL	LPAK	plastic single-ended surface-mounted package (LPAK); 4 leads	SOT669

## 4. Limiting values

**Table 4. Limiting values**

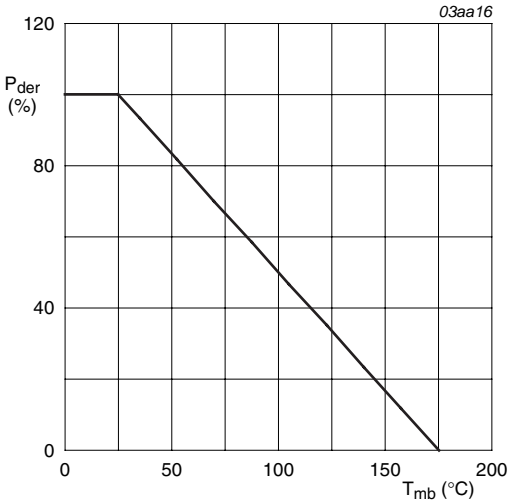
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	30	V
$V_{DGR}$	drain-gate voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	30	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; see <a href="#">Figure 1</a>	-	56	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a>	-	79	A
$I_{DM}$	peak drain current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 3</a>	-	292	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	55	W
$T_{stg}$	storage temperature		-55	175	°C
$T_j$	junction temperature		-55	175	°C
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	73	A
$I_{SM}$	peak source current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$	-	292	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ °C}$ ; $I_D = 73\text{ A}$ ; $V_{sup} \leq 30\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; unclamped	-	26	mJ



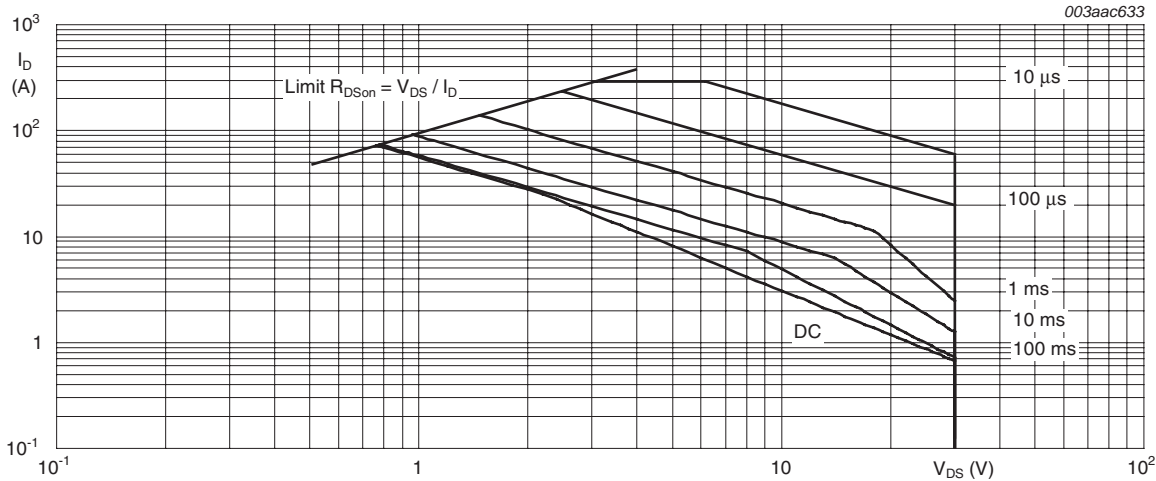
$V_{GS} \geq 10\text{ V}$

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25^{\circ}C; I_{DM}$  is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	1.4	2.25	K/W

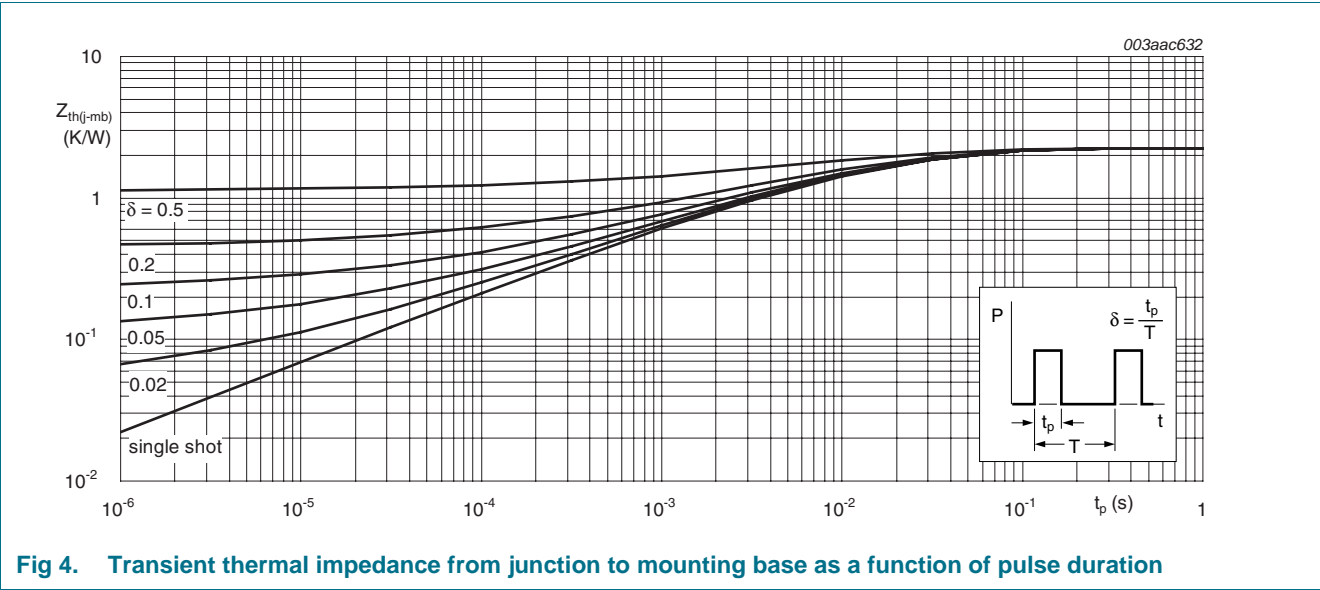


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

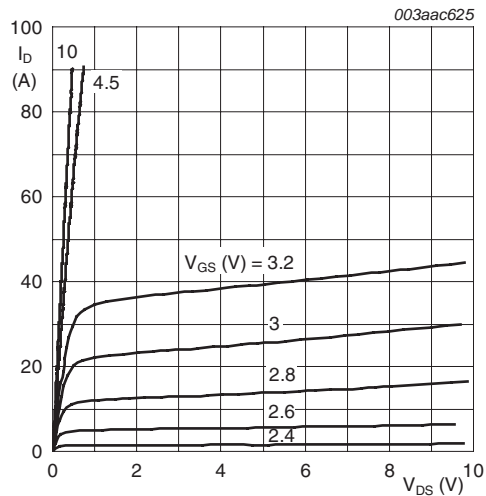
**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 20\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$ ; $t_{av} = 100\text{ ns}$	35	-	-	V
		$I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$	30	-	-	V
		$I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = -55\text{ °C}$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 11</a> and <a href="#">12</a>	1.3	1.7	2.15	V
		$I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 150\text{ °C}$ ; see <a href="#">Figure 12</a>	0.65	-	-	V
		$I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55\text{ °C}$ ; see <a href="#">Figure 12</a>	-	-	2.45	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 150\text{ °C}$	-	-	100	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 16\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$	-	-	100	nA
		$V_{GS} = -16\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_j = 25\text{ °C}$	-	6.18	7.87	m $\Omega$
		$V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_j = 150\text{ °C}$ ; see <a href="#">Figure 13</a>	-	-	10.5	m $\Omega$
		$V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_j = 25\text{ °C}$	-	4.26	6	m $\Omega$
$R_G$	gate resistance	$f = 1\text{ MHz}$	-	0.63	1.5	$\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 10\text{ A}$ ; $V_{DS} = 12\text{ V}$ ; $V_{GS} = 4.5\text{ V}$ ; see <a href="#">Figure 14</a> and <a href="#">15</a>	-	11	-	nC
		$I_D = 10\text{ A}$ ; $V_{DS} = 12\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 14</a> and <a href="#">15</a>	-	24	-	nC
		$I_D = 0\text{ A}$ ; $V_{DS} = 0\text{ V}$ ; $V_{GS} = 10\text{ V}$	-	22	-	nC
$Q_{GS}$	gate-source charge	$I_D = 10\text{ A}$ ; $V_{DS} = 12\text{ V}$ ; $V_{GS} = 4.5\text{ V}$ ; see <a href="#">Figure 14</a> and <a href="#">15</a>	-	4.2	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	2.4	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	1.8	-	nC
$Q_{GD}$	gate-drain charge		-	3.08	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 12\text{ V}$ ; see <a href="#">Figure 14</a> and <a href="#">15</a>	-	2.6	-	V
$C_{iss}$	input capacitance	$V_{DS} = 12\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $f = 1\text{ MHz}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 16</a>	-	1425	-	pF
$C_{oss}$	output capacitance		-	313	-	pF
$C_{rss}$	reverse transfer capacitance		-	155	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12\text{ V}$ ; $R_L = 0.5\text{ }\Omega$ ; $V_{GS} = 4.5\text{ V}$ ; $R_{G(ext)} = 4.7\text{ }\Omega$	-	25	-	ns
$t_r$	rise time		-	43	-	ns
$t_{d(off)}$	turn-off delay time		-	31	-	ns
$t_f$	fall time		-	11	-	ns

Table 6. Characteristics ...continued

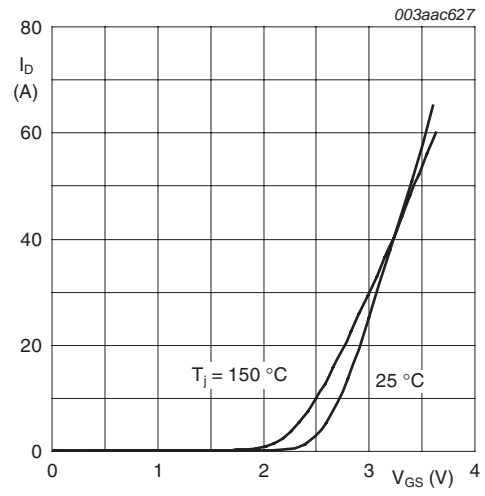
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 17</a>	-	0.88	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ;	-	32	-	ns
$Q_r$	recovered charge	$V_{DS} = 20\text{ V}$	-	25	-	nC

[1] Tested to JEDEC standards where applicable.



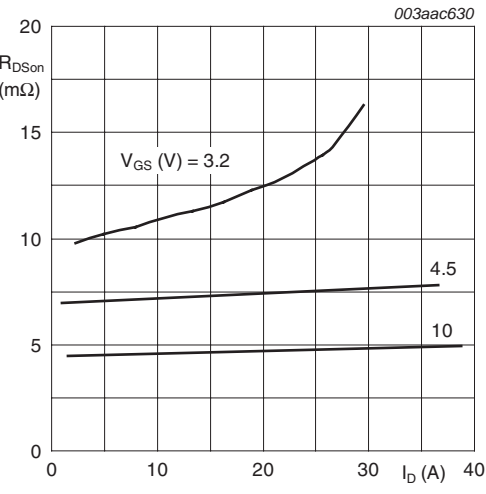
$T_j = 25\text{ }^{\circ}\text{C}$ ;  $t_p = 300\text{ }\mu\text{s}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



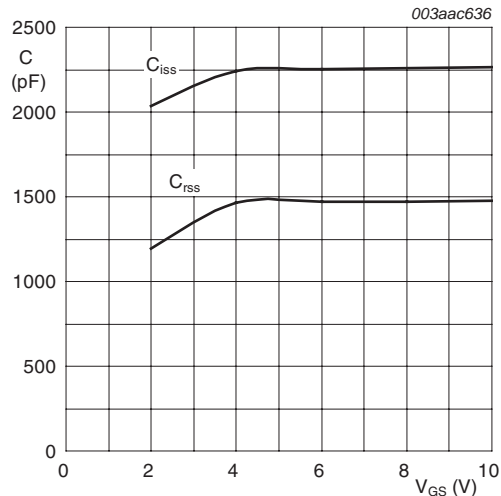
$V_{DS} = 10\text{ V}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



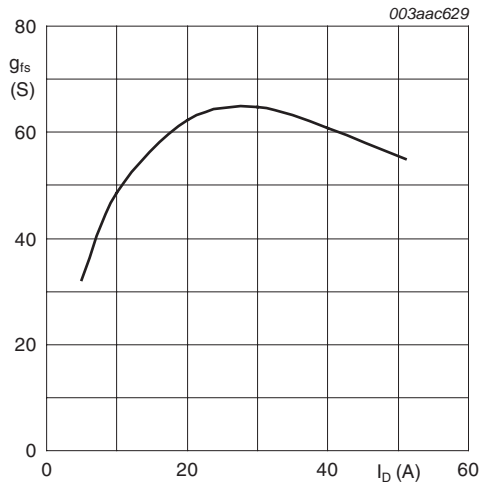
$T_j = 25\text{ }^{\circ}\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values



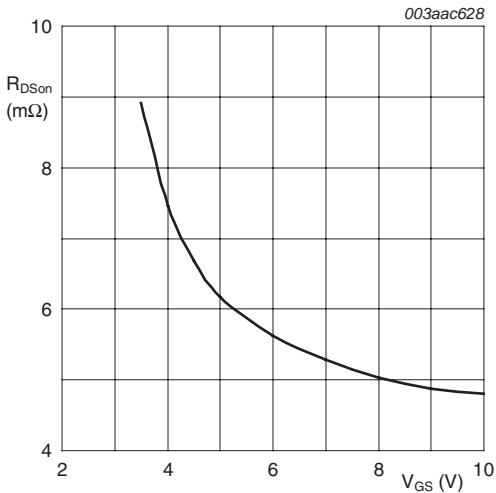
$V_{DS} = 0\text{ V}$ ;  $f = 1\text{ MHz}$

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



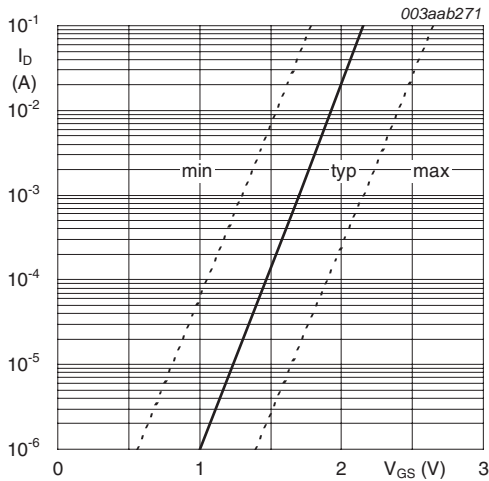
$T_j = 25\text{ }^{\circ}\text{C}; V_{DS} = 15\text{ V}$

Fig 9. Forward transconductance as a function of drain current; typical values



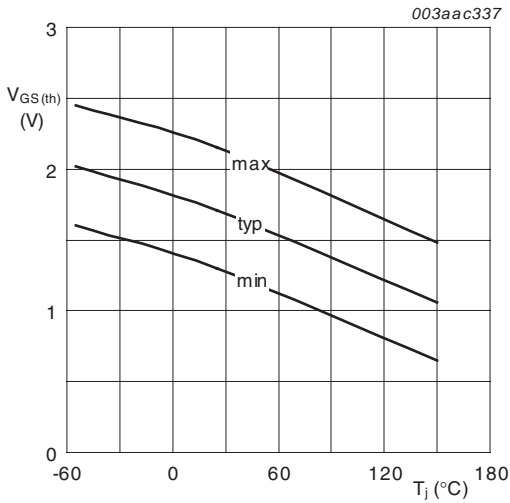
$T_j = 25\text{ }^{\circ}\text{C}; I_D = 15\text{ A}$

Fig 10. Drain-source on-state resistance as a function of gate-source voltage; typical values



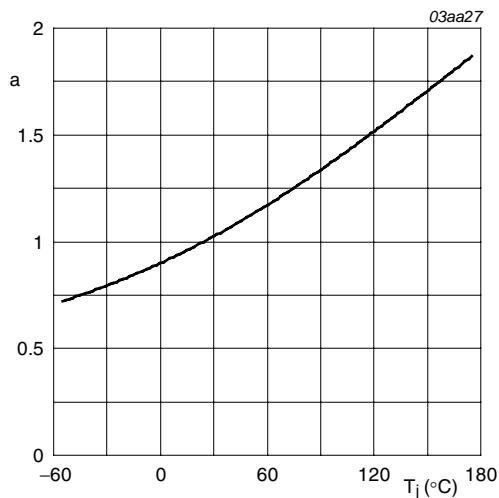
$T_j = 25\text{ }^{\circ}\text{C}; V_{DS} = 5\text{ V}$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

Fig 12. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

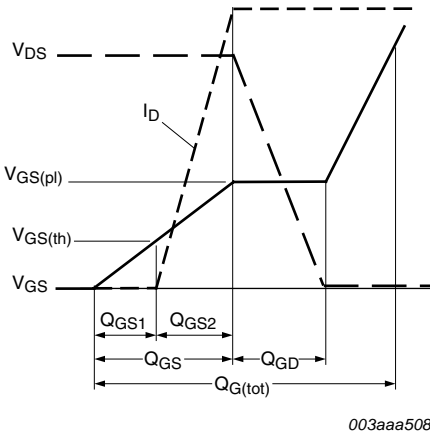
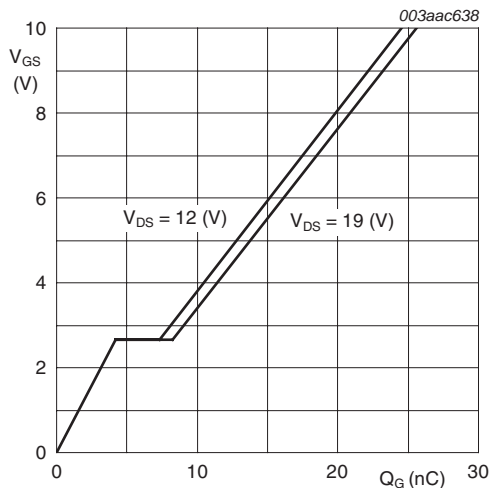
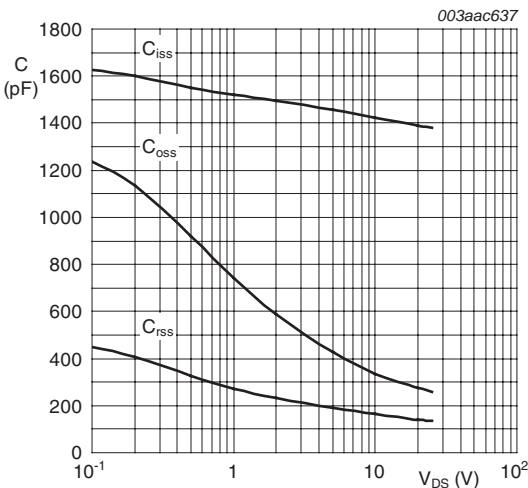


Fig 14. Gate charge waveform definitions



$$T_j = 25^{\circ}\text{C}; I_D = 10\text{ A}$$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



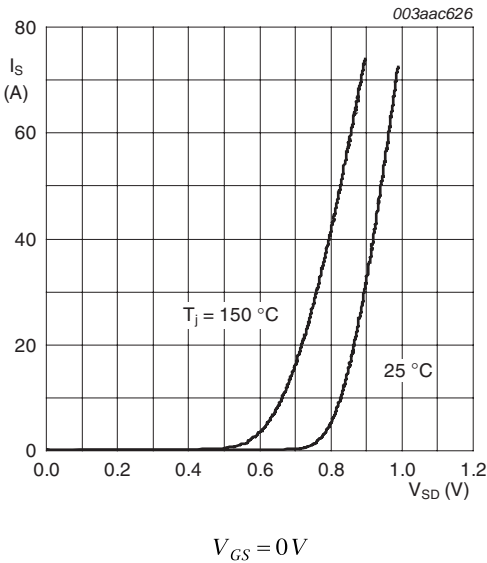


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (LFAK); 4 leads

SOT669

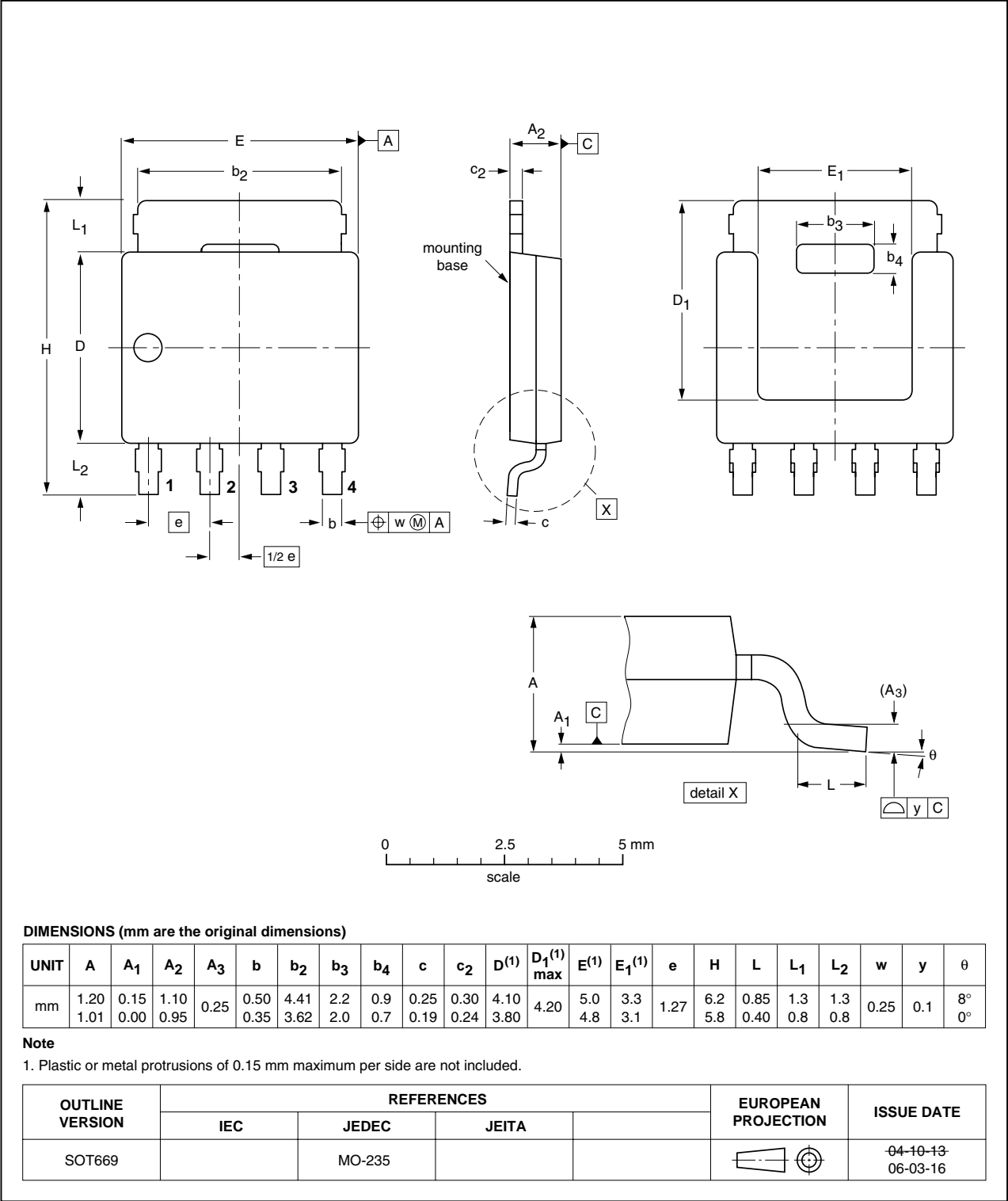


Fig 18. Package outline SOT669 (LFAK)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN6R0-30YL_3	20100104	Product data sheet	-	PSMN6R0-30YL_2
Modifications:	• Various changes to content.			
PSMN6R0-30YL_2	20090105	Product data sheet	-	PSMN6R0-30YL_1
PSMN6R0-30YL_1	20080910	Preliminary data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

## 11. Contents

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<b>1</b>	<b>Product profile</b> . . . . .	<b>1</b>
1.1	General description . . . . .	1
1.2	Features and benefits . . . . .	1
1.3	Applications . . . . .	1
1.4	Quick reference data . . . . .	1
<b>2</b>	<b>Pinning information</b> . . . . .	<b>2</b>
<b>3</b>	<b>Ordering information</b> . . . . .	<b>2</b>
<b>4</b>	<b>Limiting values</b> . . . . .	<b>2</b>
<b>5</b>	<b>Thermal characteristics</b> . . . . .	<b>4</b>
<b>6</b>	<b>Characteristics</b> . . . . .	<b>5</b>
<b>7</b>	<b>Package outline</b> . . . . .	<b>10</b>
<b>8</b>	<b>Revision history</b> . . . . .	<b>11</b>
<b>9</b>	<b>Legal information</b> . . . . .	<b>12</b>
9.1	Data sheet status . . . . .	12
9.2	Definitions . . . . .	12
9.3	Disclaimers . . . . .	12
9.4	Trademarks . . . . .	13
<b>10</b>	<b>Contact information</b> . . . . .	<b>13</b>

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